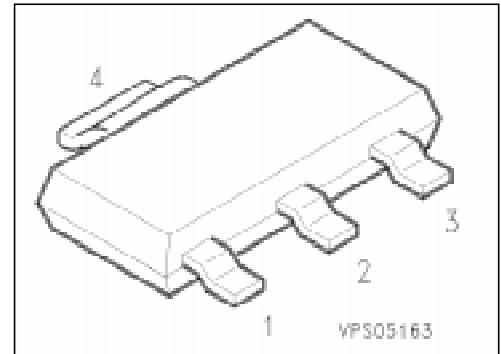


## PNP Silicon Darlington Transistors

**BCP 28**  
**BCP 48**

- For general AF applications
- High collector current
- High current gain
- Complementary types: BCP 29/49 (NPN)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration	Package <sup>1)</sup>
BCP 28 BCP 48	BCP 28 BCP 48	Q62702-C2134 Q62702-C2135		SOT-223

### Maximum Ratings

Parameter	Symbol	Values		Unit
		BCP 28	BCP 48	
Collector-emitter voltage	$V_{CE0}$	30	60	V
Collector-base voltage	$V_{CB0}$	40	80	
Emitter-base voltage	$V_{EB0}$	10	10	
Collector current	$I_C$	500		mA
Peak collector current	$I_{CM}$	800		
Base current	$I_B$	100		
Peak base current	$I_{BM}$	200		
Total power dissipation, $T_s = 124\text{ °C}^2)$	$P_{tot}$	1.5		W
Junction temperature	$T_j$	150		°C
Storage temperature range	$T_{stg}$	- 65 ... + 150		

### Thermal Resistance

Junction - ambient <sup>2)</sup>	$R_{th\ JA}$	≤ 75	K/W
Junction - soldering point	$R_{th\ JS}$	≤ 17	

<sup>1)</sup> For detailed information see chapter Package Outlines.

<sup>2)</sup> Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm<sup>2</sup> Cu.

## Electrical Characteristics

at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

### DC characteristics

Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CE0}$				V
BCP 28		30	–	–	
BCP 48		60	–	–	
Collector-base breakdown voltage <sup>1)</sup> $I_C = 100\text{ }\mu\text{A}, I_B = 0$	$V_{(BR)CB0}$				
BCP 28		40	–	–	
BCP 48		80	–	–	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EB0}$	10	–	–	
Collector-base cutoff current $V_{CB} = 30\text{ V}, I_E = 0$	$I_{CB0}$				nA
BCP 28		–	–	100	nA
$V_{CB} = 60\text{ V}, I_E = 0$					nA
BCP 48		–	–	100	nA
$V_{CB} = 30\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$					$\mu\text{A}$
BCP 28		–	–	10	$\mu\text{A}$
$V_{CB} = 60\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$					$\mu\text{A}$
BCP 48		–	–	10	$\mu\text{A}$
Emitter-base cutoff current $V_{EB} = 4\text{ V}, I_C = 0$	$I_{EB0}$	–	–	100	nA
DC current gain <sup>1)</sup> $I_C = 100\text{ }\mu\text{A}, V_{CE} = 1\text{ V}$	$h_{FE}$				–
BCP 28		4000	–	–	
BCP 48		2000	–	–	
$I_C = 10\text{ mA}, V_{CE} = 5\text{ V}$					
BCP 28		10000	–	–	
BCP 48		4000	–	–	
$I_C = 100\text{ mA}, V_{CE} = 5\text{ V}$					
BCP 28		20000	–	–	
BCP 48		10000	–	–	
$I_C = 500\text{ mA}, V_{CE} = 5\text{ V}$					
BCP 28		4000	–	–	
BCP 48		2000	–	–	
Collector-emitter saturation voltage $I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	$V_{CEsat}$	–	–	1.0	V
Base-emitter saturation voltage $I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	$V_{BEsat}$	–	–	1.5	

<sup>1)</sup> Pulse test conditions:  $t \leq 300\text{ }\mu\text{s}, D \leq 2\%$ .

**Electrical Characteristics**at  $T_A = 25\text{ °C}$ , unless otherwise specified.

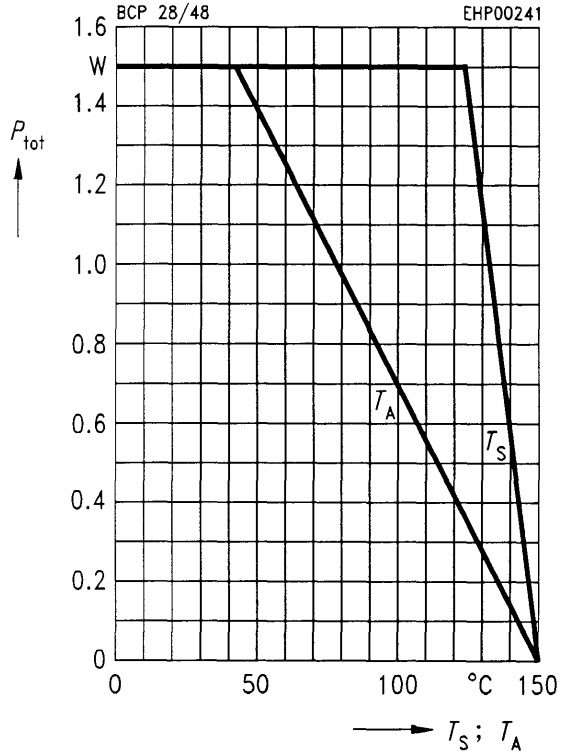
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**AC characteristics**

Transition frequency $I_C = 50\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 100\text{ MHz}$	$f_t$	–	200	–	MHz
Output capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{obo}$	–	8	–	pF

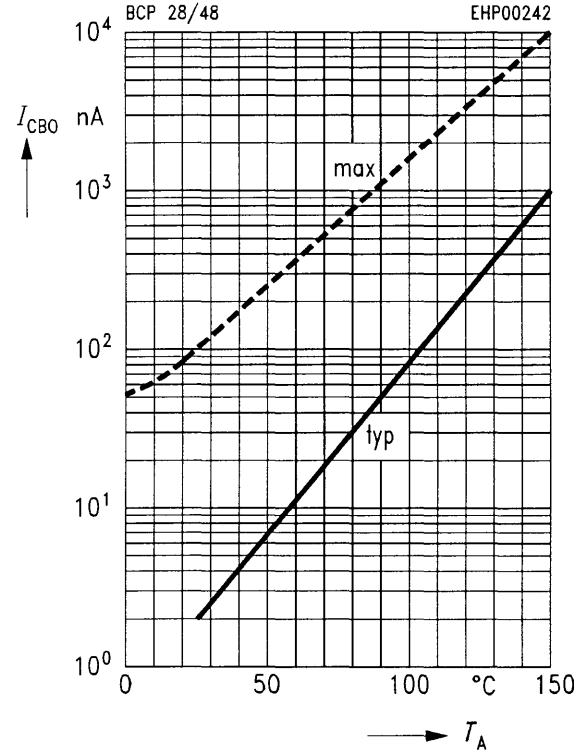
**Total power dissipation  $P_{tot} = f(T_A^*; T_S)$**

\* Package mounted on epoxy



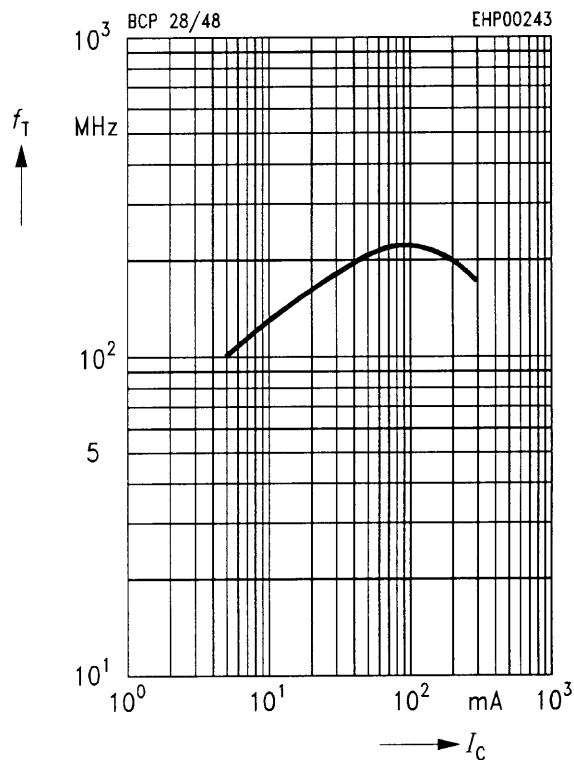
**Collector cutoff current  $I_{CBO} = f(T_A)$**

$V_{CB} = V_{CE\ max}$

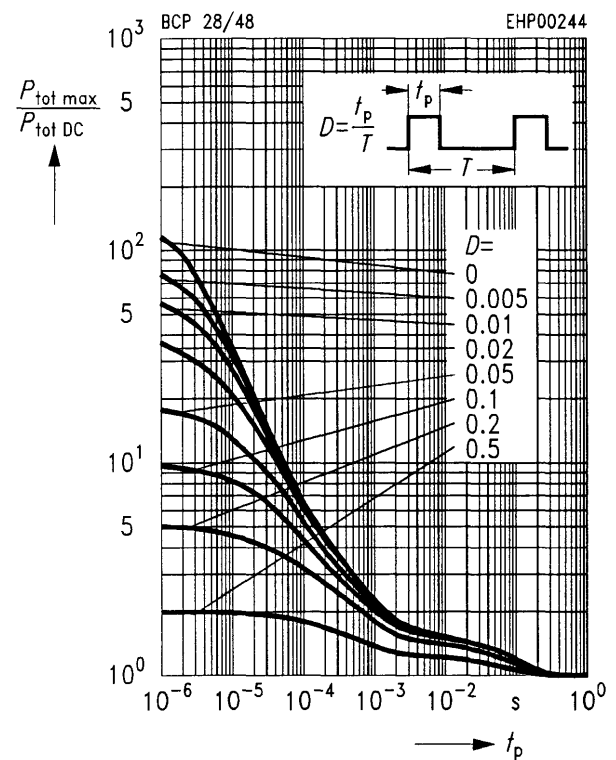


**Transition frequency  $f_T = f(I_C)$**

$V_{CE} = 5\ V$

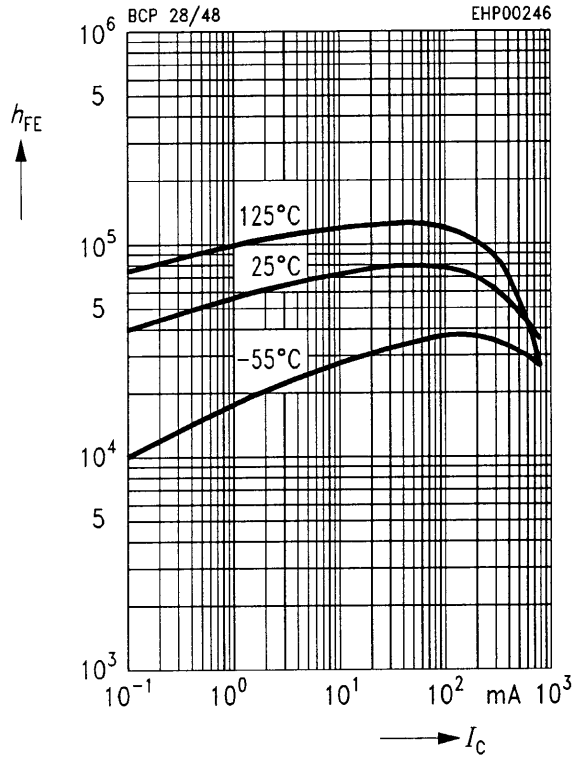


**Permissible pulse load  $P_{tot\ max}/P_{tot\ DC} = f(t_p)$**



**DC current gain  $h_{FE} = f(I_C)$**

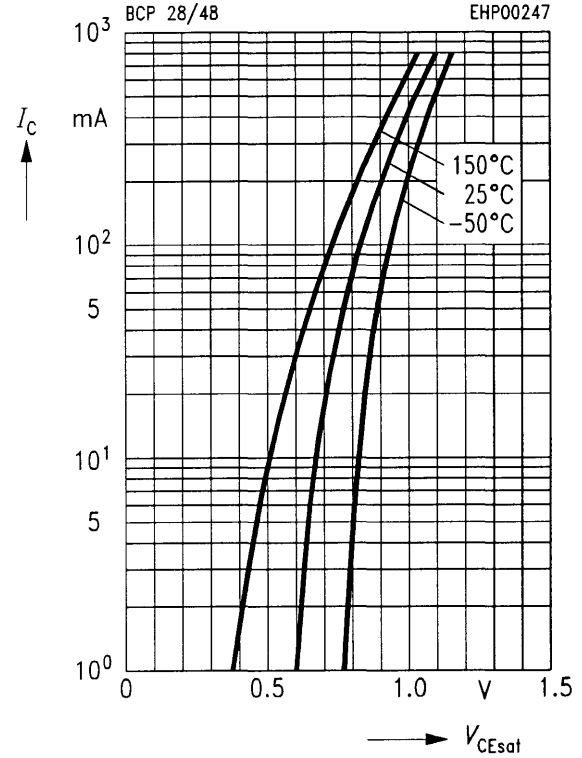
$V_{CE} = 5\text{ V}$



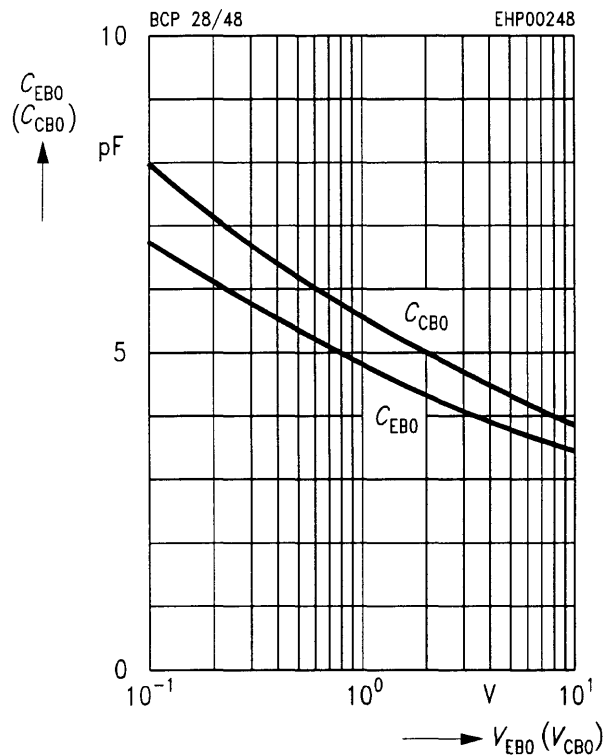
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat})$

$h_{FE} = 1000$



**Collector-base capacitance  $C_{CB0} = f(V_{CB0})$**   
**Emitter-base capacitance  $C_{EB0} = f(V_{EB0})$**



**Base-emitter saturation voltage**

$I_C = f(V_{BEsat})$

$h_{FE} = 1000$

